



TO-92 Plastic-Encapsulate Transistors

PCR 100- 6 , - 8 Silicon Planar PNP Thyristor

FEATURES

Current- I_{GT} : 200 μ A

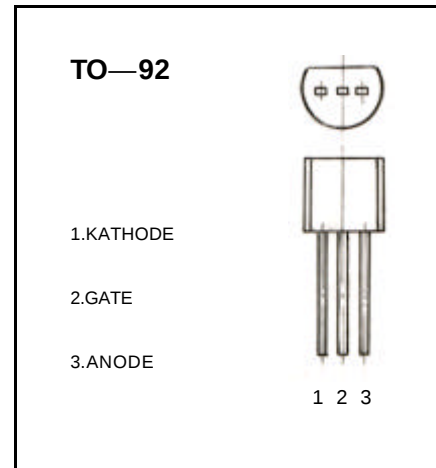
I_{TRMS} : 0.8 A

V_{DRM} : PCR100-6 : 400 V

PCR100-8 : 600 V

Operating and storage junction temperature range

T_J , T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage PCR100-6 PCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=10 \mu A, V_{MAX}=1010 V$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20 mA, A_v = 7 V$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7V$	5	15	μA
			15	30	μA
			30	80	μA
			80	200	μA

* Forward current applied for 1 ms maximum duration , duty cycle $\leq 1\%$.

Typical Characteristics

PCR100-6,-8

FIGURE 1-PCR100-7, PCR100-8 CURRENT DERATING
(REFERENCE: CASE TEMPERATURE)

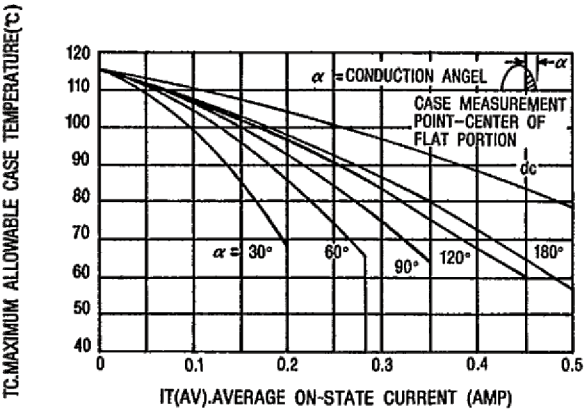
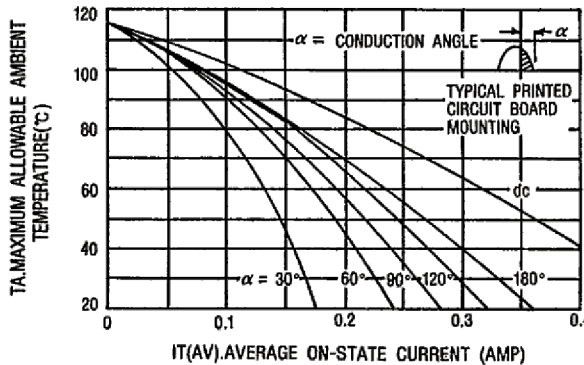
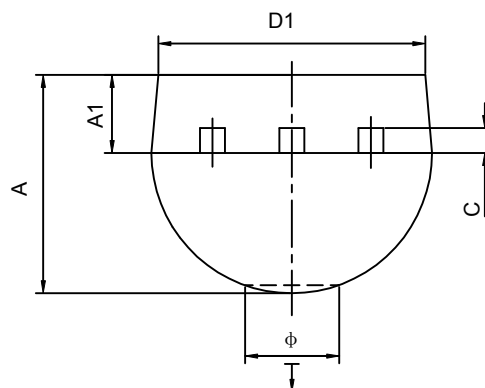
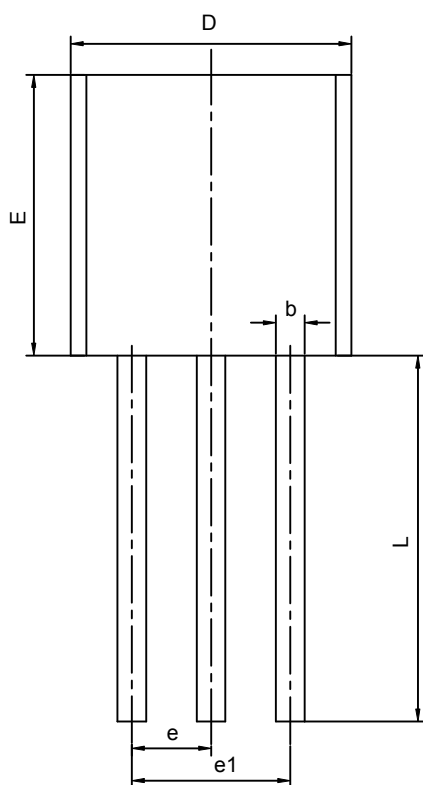


FIGURE 2-PCR100-7, PCR100-8 CURRENT DERATING
(REFERENCE: AMBIENT TEMPERATURE)



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
↓	0.000	0.380	0.000	0.015